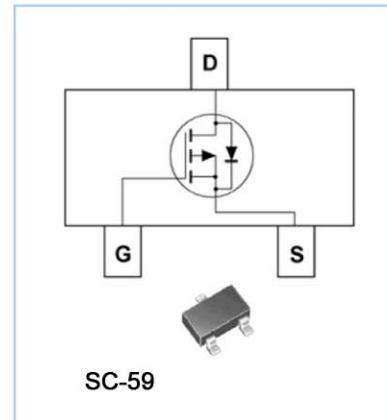


## Feature

- -16V/-3A, R<sub>DS(ON)</sub> = 160m Ω (MAX) @V<sub>GS</sub> = -4.5V.  
R<sub>DS(ON)</sub> = 240m Ω (MAX) @V<sub>GS</sub> = -2.5V.
- Super High dense cell design for extremely low R<sub>DS(ON)</sub>
- Reliable and Rugged
- SC-59 for Surface Mount Package



## Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

## Absolute Maximum Ratings

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V <sub>DS</sub>	-16	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Drain Current-Continuous	I <sub>D</sub>	-3	A

## Electrical Characteristics

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V	-	-	-5	μA
Gate Body Leakage Current, Forward	IGSSF	V <sub>GS</sub> =8V, V <sub>DS</sub> =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V <sub>GS</sub> =-8V, V <sub>DS</sub> =0V	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250μA	-0.45	-	-1.5	V
Static Drain-source	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.0A	-	120	160	mΩ
On-Resistance		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A	-	190	240	mΩ
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1.25A			-1.8	V



## Typical Characteristics

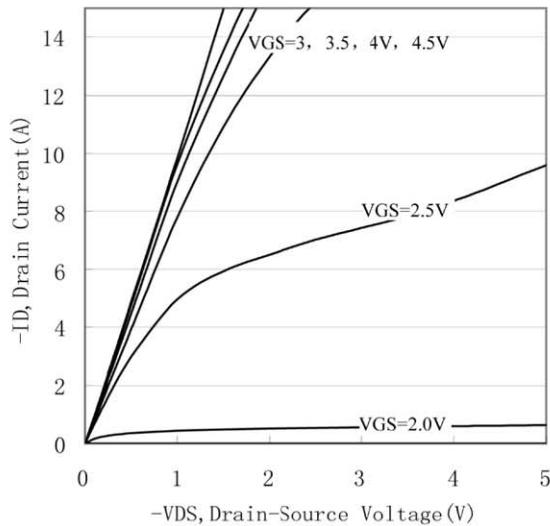


Figure 1. Output Characteristics

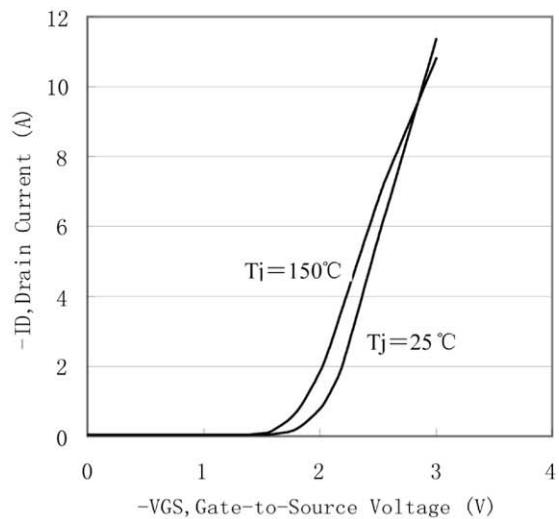


Figure 2. Transfer Characteristics

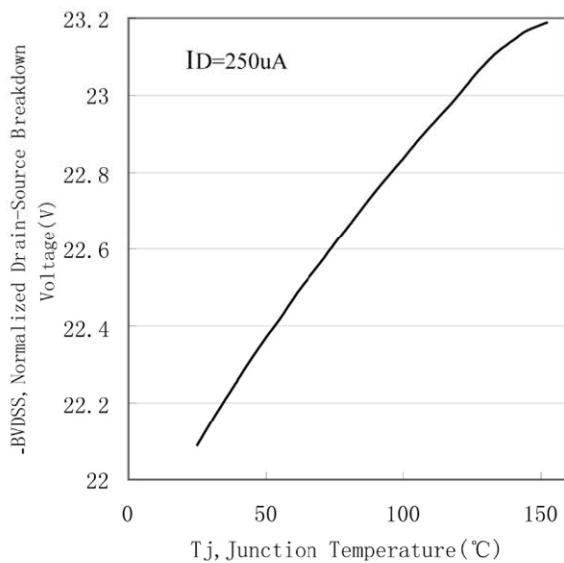


Figure 3. Breakdown Voltage Variation with Temperature

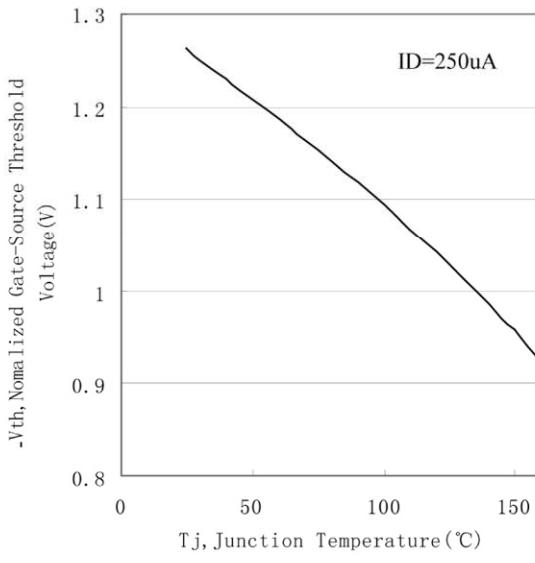
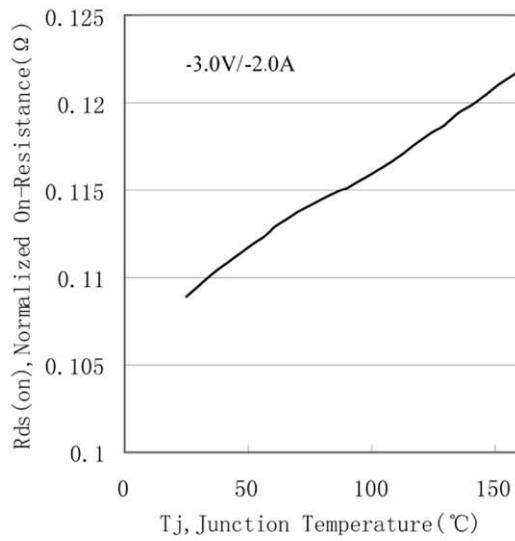


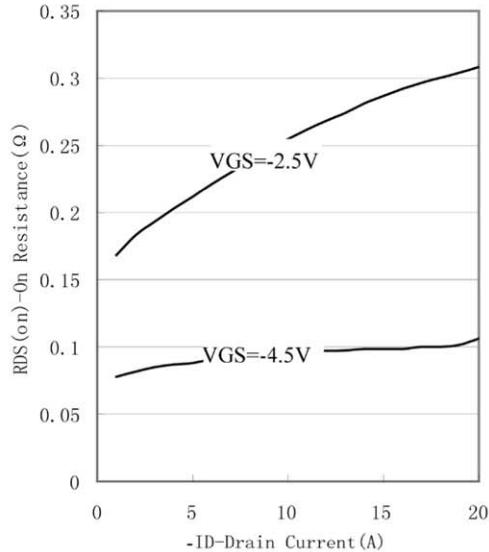
Figure 4. Gate Threshold Variation with Temperature



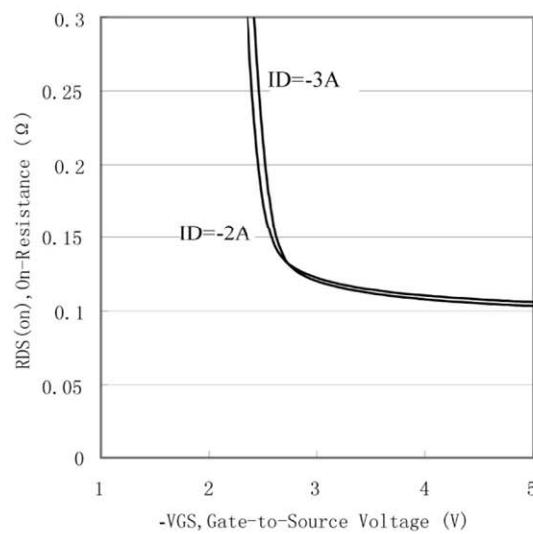
## Typical Characteristics



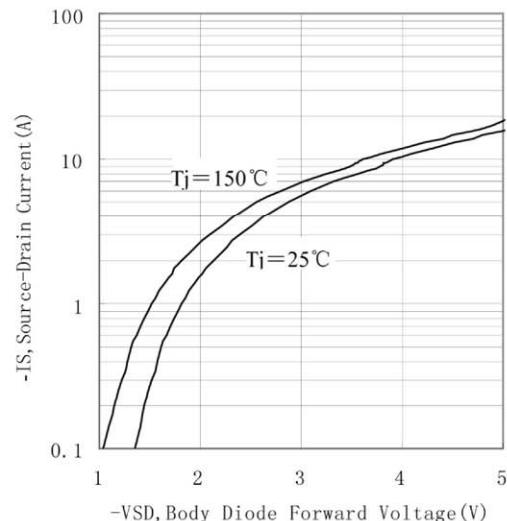
**Figure 5.** On-Resistance Variation with Temperature



**Figure 6.** On-Resistance vs. Drain Current



**Figure 7.** On-Resistance vs. Gate-to-Source Voltage



**Figure 8.** Source-Drain Diode Forward Voltage

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